



44 FARRAND STREET  
BLOOMFIELD, NJ 07003  
(973) 748-5089

<http://www.nteinc.com>

**2N3771 & 2N3772  
Silicon NPN Transistor  
High Power Audio Amplifier  
TO-3 Type Package**

**Description:**

The 2N3771 and 2N3772 are silicon epitaxial-base NPN transistors in a TO-3 type case intended for linear amplifiers and inductive switching applications

**Absolute Maximum Ratings:**

Collector-Emitter Voltage ( $I_E = 0$ ),  $V_{CEO}$

1N3771 .....	40V
1N3772 .....	60V

Collector-Emitter Voltage ( $V_{BE} = -1.5V$ ),  $V_{CEV}$

1N3771 .....	50V
1N3772 .....	80V

Collector-Base Voltage ( $I_B = 0$ ),  $V_{CBO}$

1N3771 .....	50V
1N3772 .....	100V

Emitter-Base Voltage ( $I_C = 0$ ),  $V_{EBO}$

1N3771 .....	5V
1N3772 .....	7V

Collector Current,  $I_C$

1N3771 .....	30A
1N3772 .....	20A

Peak Collector Current,  $I_{CM}$

Base Current,  $I_B$

1N3771 .....	7.5A
1N3772 .....	5A

Peak Base Current,  $I_{BM}$

Total Device Dissipation ( $T_C \leq +25^\circ C$ ),  $P_D$

Operating Junction Temperature Range,  $T_J$

Storage Temperature Range,  $T_{stg}$

Thermal Resistance, Junction-to-Case,  $R_{thJC}$

**Electrical Characteristics:** ( $T_C = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Collector Cutoff Current 1N3771 1N3772 All Devices	$I_{CEV}$	$V_{BE} = -1.5\text{V}$	$V_{CB} = 50\text{V}$	-	-	2	mA
			$V_{CB} = 100\text{V}$	-	-	5	mA
			$V_{CB} = 30\text{V}, T_J = +150^\circ\text{C}$	-	-	10	mA
Collector Cutoff Current 1N3771 1N3772	$I_{CEO}$	$I_B = 0$	$V_{CB} = 30\text{V}$	-	-	10	mA
			$V_{CB} = 50\text{V}$	-	-	10	mA
Collector Cutoff Current 1N3771 1N3772	$I_{CBO}$	$I_E = 0$	$V_{CB} = 50\text{V}$	-	-	4	mA
			$V_{CB} = 100\text{V}$	-	-	5	mA
Emitter Cutoff Current 1N3771 1N3772	$I_{EBO}$	$I_C = 0$	$V_{CB} = 5\text{V}$	-	-	5	mA
			$V_{CB} = 7\text{V}$	-	-	5	mA
Collector-Emitter Sustaining Voltage 1N3771 1N3772	$V_{CEO(\text{sus})}$	$I_C = 200\text{mA}, I_B = 0$ , Note 1		40	-	-	V
				60	-	-	V
Collector-Emitter Sustaining Voltage 1N3771 1N3772	$V_{CEV(\text{sus})}$	$V_{BE} = -1.5\text{V}, I_C = 200\text{mA}, R_{BE} = 100\Omega$ , Note 1		50	-	-	V
				80	-	-	V
Collector-Emitter Sustaining Voltage 1N3771 1N3772	$V_{CER(\text{sus})}$	$I_C = 200\text{mA}, R_{BE} = 100\Omega$ , Note 1		45	-	-	V
				70	-	-	V
Collector-Emitter Saturation Voltage 1N3771 1N3772	$V_{CE(\text{sat})}$	Note 1	$I_C = 15\text{A}, I_B = 1.5\text{A}$	-	-	2	V
			$I_C = 30\text{A}, I_B = 6\text{A}$	-	-	4	V
			$I_C = 10\text{A}, I_B = 1\text{A}$	-	-	1.4	V
			$I_C = 20\text{A}, I_B = 4\text{A}$	-	-	4	V
Base-Emitter Voltage 1N3771 1N3772	$V_{BE}$	$V_{CE} = 4\text{V}$ , Note 1	$I_C = 15\text{A}$	-	-	2.7	V
			$I_C = 10\text{A}$	-	-	2.7	V
DC Current Gain 1N3771 1N3772	$h_{FE}$	$V_{CE} = 4\text{V}$ , Note 1	$I_C = 15\text{A}$	15	-	60	
			$I_C = 30\text{A}$	5	-	-	
			$I_C = 10\text{A}$	15	-	60	
			$I_C = 20\text{A}$	5	-	-	
Small Signal Current Gain	$h_{FE}$	$I_C = 1\text{A}, V_{CE} = 4\text{V}, f = 1\text{kHz}$		40	-	-	
Transition Frequency	$f_T$	$I_C = 1\text{A}, V_{CE} = 4\text{V}, f = 50\text{kHz}$		0.2	-	-	MHz
Second Breakdown Collector Current	$I_{s/b}$	$V_{CE} = 25\text{V}, t = 1\text{s}$ (non-repetitive)		6	-	-	A

Note 1. Pulse Test: Pulse Width = 300μs. Duty Cycle ≤ 2%.

